

# SOT223 PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

## FZT788B

ISSUE 3 - OCTOBER 1995

### FEATURES

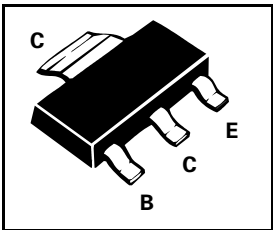
- \* Low equivalent on-resistance;  $R_{CE(sat)}$  **93mΩ at 3A**
- \* Gain of 300 at  $I_C=2$  Amps and Very low saturation voltage

### APPLICATIONS

- \* Battery powered circuits

COMPLEMENTARY TYPE – FZT688B

PARTMARKING DETAIL – FZT788B



### ABSOLUTE MAXIMUM RATINGS.

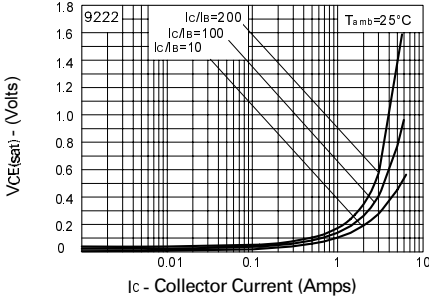
| PARAMETER                                  | SYMBOL         | VALUE       | UNIT        |
|--|----------------|-------------|-------------|
| Collector-Base Voltage                     | $V_{CBO}$      | -15         | V           |
| Collector-Emitter Voltage                  | $V_{CEO}$      | -15         | V           |
| Emitter-Base Voltage                       | $V_{EBO}$      | -5          | V           |
| Peak Pulse Current                         | $I_{CM}$       | -8          | A           |
| Continuous Collector Current               | $I_C$          | -3          | A           |
| Power Dissipation at $T_{amb}=25^{\circ}C$ | $P_{tot}$      | 2           | W           |
| Operating and Storage Temperature Range    | $T_j; T_{stg}$ | -55 to +150 | $^{\circ}C$ |

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ )

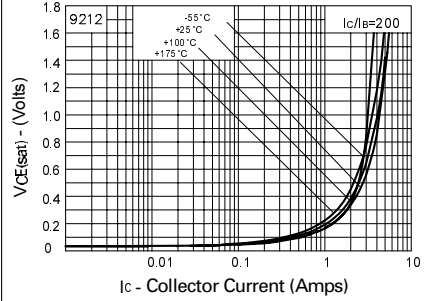
| PARAMETER                             | SYMBOL                | MIN.                     | TYP.      | MAX.                            | UNIT     | CONDITIONS.  |
|---------------------------------------|-----------------------|--------------------------|-----------|---------------------------------|----------|--|
| Collector-Base Breakdown Voltage      | $V_{(BR)CBO}$         | -15                      |           |                                 | V        | $I_C=-100\mu A$  |
| Collector-Emitter Breakdown Voltage   | $V_{(BR)CEO}$         | -15                      |           |                                 | V        | $I_C=-10mA^*$  |
| Emitter-Base Breakdown Voltage        | $V_{(BR)EBO}$         | -5                       |           |                                 | V        | $I_E=-100\mu A$  |
| Collector Cut-Off Current             | $I_{CBO}$             |                          |           | -0.1                            | $\mu A$  | $V_{CE}=-10V$  |
| Emitter Cut-Off Current               | $I_{EBO}$             |                          |           | -0.1                            | $\mu A$  | $V_{EB}=-4V$   |
| Collector-Emitter Saturation Voltage  | $V_{CE(sat)}$         |                          |           | -0.15<br>-0.25<br>-0.45<br>-0.5 | V        | $I_C=-0.5A, I_B=-2.5mA^*$<br>$I_C=-1A, I_B=-5mA^*$<br>$I_C=-2A, I_B=-10mA^*$<br>$I_C=-3A, I_B=-50mA^*$     |
| Base-Emitter Saturation Voltage       | $V_{BE(sat)}$         |                          |           | -0.9                            | V        | $I_C=-1A, I_B=-5mA^*$  |
| Base-Emitter Turn-On Voltage          | $V_{BE(on)}$          |                          | -0.75     |                                 | V        | $I_C=-1A, V_{CE}=-2V^*$  |
| Static Forward Current Transfer Ratio | $h_{FE}$              | 500<br>400<br>300<br>150 |           | 1500                            |          | $I_C=-10mA, V_{CE}=-2V^*$<br>$I_C=-1A, V_{CE}=-2V^*$<br>$I_C=-2A, V_{CE}=-2V^*$<br>$I_C=-6A, V_{CE}=-2V^*$ |
| Transition Frequency                  | $f_T$                 | 100                      |           |                                 | MHz      | $I_C=-50mA, V_{CE}=-5V$<br>$f=50MHz$   |
| Input Capacitance                     | $C_{ibo}$             |                          | 225       |                                 | pF       | $V_{EB}=-0.5V, f=1MHz$   |
| Output Capacitance                    | $C_{obo}$             |                          | 25        |                                 | pF       | $V_{CB}=-10V, f=1MHz$  |
| Switching Times                       | $t_{on}$<br>$t_{off}$ |                          | 35<br>400 |                                 | ns<br>ns | $I_C=-500mA, I_{B1}=-50mA$<br>$I_{B2}=-50mA, V_{CC}=-10V$  |

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$   
Spice parameter data is available upon request for this device

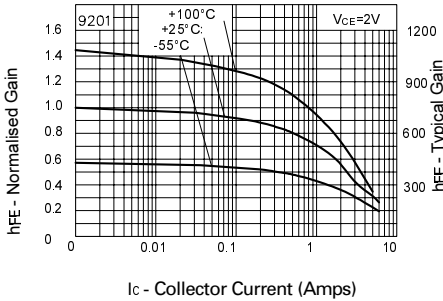
## TYPICAL CHARACTERISTICS



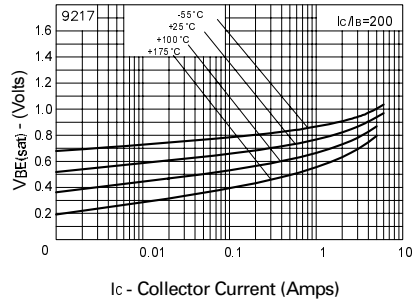
**VCE(sat) v IC**



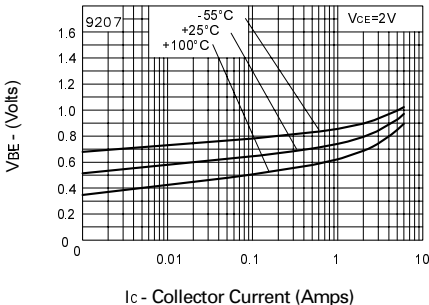
**VCE(sat) v IC**



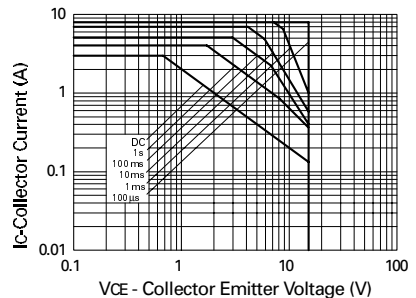
**hFE v IC**



**VBE(sat) v IC**



**VBE(on) v IC**



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